

February 1, 2002

TO: Commissioner of Patents and Trademarks
Washington, D.C. 20231

FROM: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

SUBJECT: **Reissue Application of:**
Patent #: 6,019,906
Issue Date: Feb. 1, 2000
Inventor: Syun-Ming Jang, Ming-Hsin Huang
Examiner:
Art Unit:
Title: Hard Masking Method for Forming Patterned Oxygen
Containing Plasma Etchable Layer

PRELIMINARY AMENDMENT

This regards the Reissue Application of the above identified patent. Please amend
the above-identified patent as follows:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States
Postal Service as first class mail in an envelope addressed to: Commissioner of
Patents and Trademarks, Washington, D.C. 20231 on February 1, 2002.

Signature: 
Stephen B. Ackerman, Reg. No. 37,761

Date: 2/1/02

STATUS OF CLAIMS

Claims 1-27 are pending.

PLEASE AMEND THE CLAIMS AS FOLLOWS:

4. (AMENDED) The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an [an oxygen containing plasma etchable material selected from the group consisting of oxygen containing plasma etchable conductor materials, oxygen containing plasma etchable semiconductor materials, and] oxygen containing plasma etchable dielectric material[s]

Add claims 17-27 as follows:

17. The method of Claim 4 wherein said oxygen containing plasma etchable dielectric material is a low dielectric constant material.

18. The method of Claim 17 wherein said low dielectric constant material is a polyimide organic polymer spin-on polymer dielectric material.

19. The method of Claim 17 wherein said low dielectric constant material is a spin-on low dielectric constant material.

20. The method of Claim 19 wherein said spin-on low dielectric constant material is a poly (arylene ether) organic polymer spin-on polymer dielectric material.

21. The method of Claim 19 wherein said spin-on low dielectric constant material is a fluorinated poly (arylene ether) organic polymer spin-on polymer dielectric material.

22. The method of Claim 17 wherein said low dielectric constant material is an amorphous carbon dielectric material.

23. The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an oxygen containing plasma etchable conductor material.

24. The method of Claim 1 wherein the oxygen containing plasma etchable microelectronics layer is formed from an oxygen containing plasma etchable semiconductor material.

25. The method of Claim 19 wherein said spin-on low dielectric constant material is a hydrogen silsesquioxane spin-on-glass dielectric material.

26. The method of Claim 19 wherein said spin-on low dielectric constant material is a carbon bonded hydrogen silsesquioxane spin-on-glass dielectric material.

27. The method of Claim 19 wherein said spin-on low dielectric constant material is a carbon bonded fluorocarbon silsesquioxane spin-on-glass dielectric material.

REMARKS

Please enter this Preliminary Amendment in the above identified Reissue Application. All claims are believed to be allowable, and allowance of the claims is so requested.

Support in the disclosure for the amended and new claims may be found at:

Amended Claim 4: Column 7, lines 53-58

New Claim 17: column 11, lines 45-46

New Claim 18: column 11, lines 48-49

New Claim 19: column 11, lines 43 and 47-52

New Claim 20: column 11, lines 49-50

New Claim 21: column 11, lines 50-52

New Claim 22: column 11, lines 52-53

New Claim 23: column 7, lines 55-56

New Claim 24: column 7, lines 56-57

New Claim 25: column 11, lines 55-56

New Claim 26: column 11, lines 56-58

New Claim 27: column 11, lines 58-59

It is requested that should there be any problems with this Amendment, please call the undersigned Attorney at (845) 452-5863.

Respectfully submitted,



Stephen B. Ackerman, Reg. No. 37,761